

HAT2204C

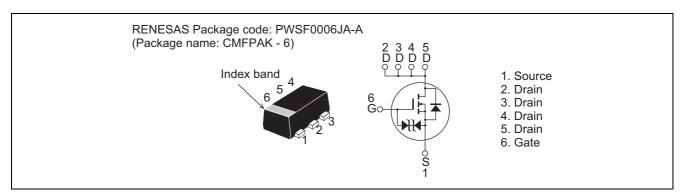
Silicon N Channel MOS FET Power Switching

REJ03G0448-0500 Rev.5.00 May 10, 2007

Features

- Low on-resistance $R_{DS(on)} = 26m \Omega \text{ typ.} (at V_{GS} = 4.5 \text{ V})$
- Low drive current
- High density mounting
- 1.8 V gate drive device

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source voltage	V _{DSS}	12	V
Gate to Source voltage	V _{GSS}	±8	V
Drain current	I _D	3.5	А
Drain peak current	I _{D (pulse)} Note1	14	А
Body - Drain diode reverse Drain current	I _{DR}	3.5	А
Channel dissipation	Pch Note2	900	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. When using the glass epoxy board (FR4 40 x 40 x 1.6mm)

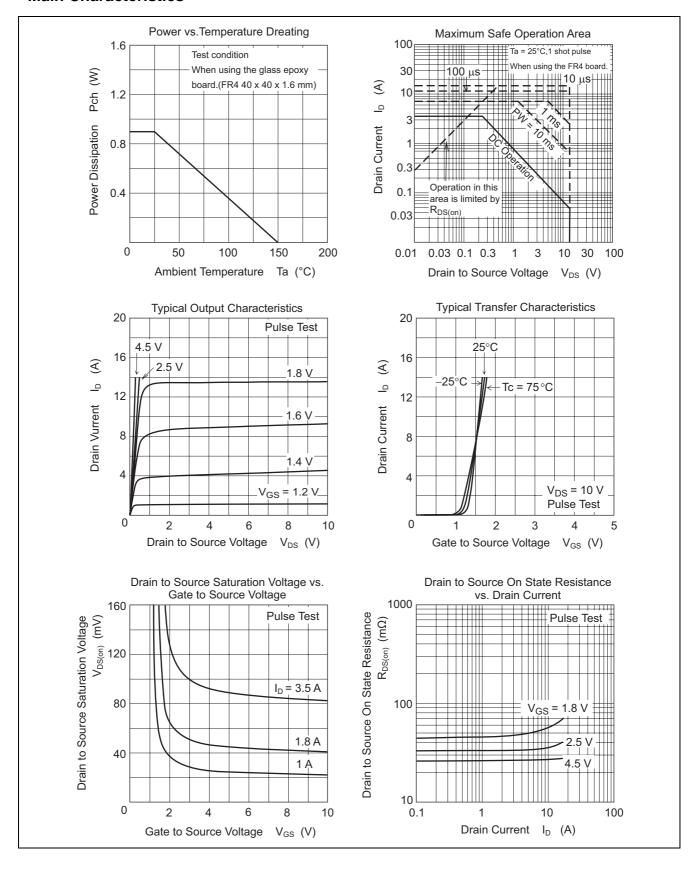
Electrical Characteristics

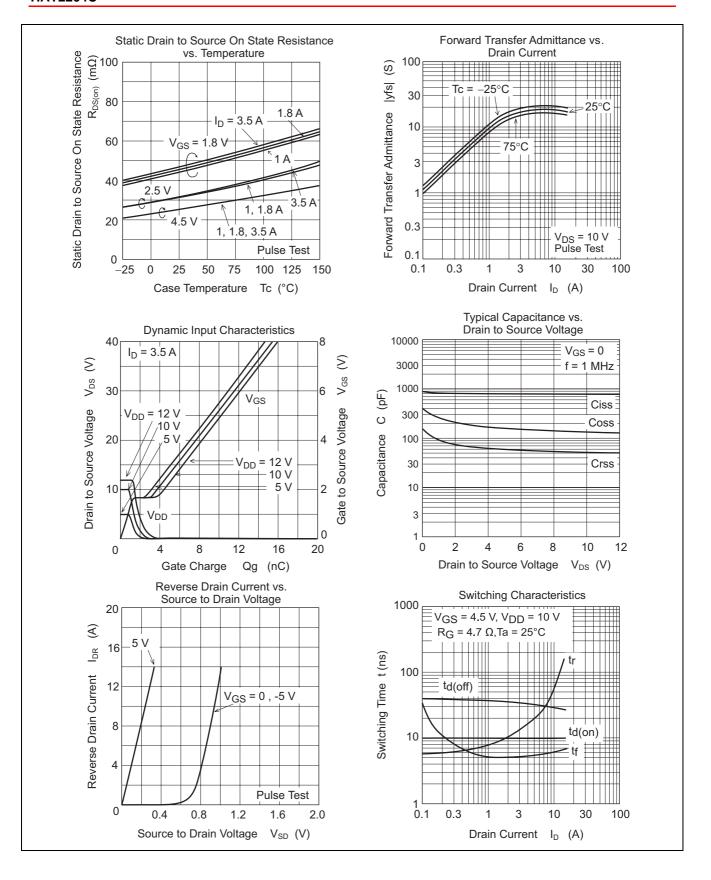
 $(Ta = 25^{\circ}C)$

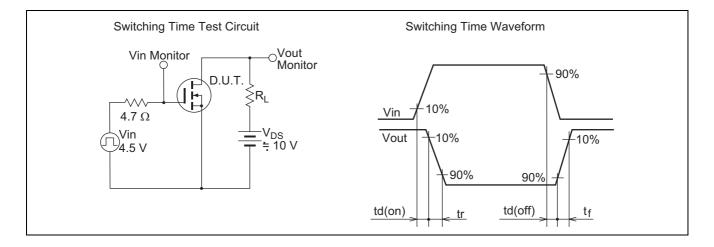
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	12	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to Source breakdown voltage	$V_{(BR)GSS}$	±8				$I_G = \pm 10 \ \mu A, \ V_{DS} = 0$
Gate to Source leakage current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 6.4 \text{ V}, V_{DS} = 0$
Drain to Source leakage current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 12 \text{ V}, V_{GS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	0.3	_	1.2	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Drain to Source on state resistance	R _{DS(on)}	_	26	34	mΩ	$I_D = 1.8 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note3}}$
	R _{DS(on)}	_	34	44	mΩ	$I_D = 1.8 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
	R _{DS(on)}	_	45	69	mΩ	$I_D = 1.8 \text{ A}, V_{GS} = 1.8 \text{ V}^{Note3}$
Forward transfer admittance	yfs	8.5	13	_	S	$I_D = 1.8 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	770	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	115	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	50	_	pF	f = 1 MHz
Turn - on delay time	$t_{d(on)}$	_	10	_	ns	$I_D = 1.8 \text{ A}, V_{GS} = 4.5 \text{ V}$
Rise time	t _r	_	9.5	_	ns	$V_{DS} = 10 \text{ V}, R_{L} = 5.6 \Omega,$
Turn - off delay time	$t_{d(off)}$	_	36	_	ns	$Rg = 4.7 \Omega$
Fall time	t _f	_	5	_	ns	
Total Gate charge	Qg	_	9	_	nC	V _{DD} = 10 V
Gate to Source charge	Qgs	_	1.5	_	nC	$V_{GS} = 4.5 \text{ V}$
Gate to Drain charge	Qgd		2		nC	I _D = 3.5 A
Body - Drain diode forward voltage	V_{DF}	_	0.8	1.1	V	$I_F = 3.5 \text{ A}, V_{GS} = 0^{\text{Note3}}$

Notes: 3. Pulse test

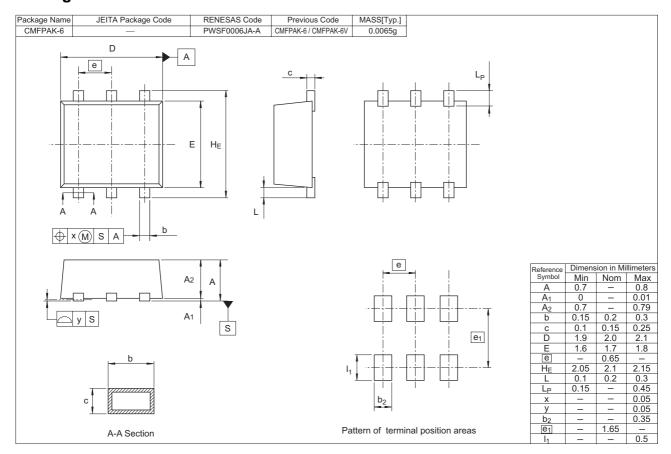
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2204C-EL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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